



## ATTACHMENT B

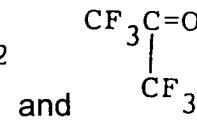
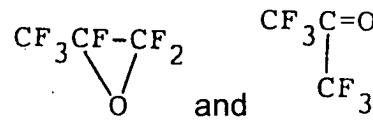
### Amendment to the Claims

*This listing of claims will replace all prior versions, and listings, of claims in the application:*

1-10. (Canceled)

11. (Withdrawn) A chamber cleaning gas comprising at least one gas

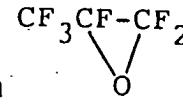
selected from the group consisting of  $\text{CF}_3\text{CF}=\text{CF}_2$ ,



wherein the chamber cleaning gas removes reaction byproducts selected from the group consisting of silicon, polysilicon, tungsten, titanium and their oxides, nitrides and carbides attached to the wall of the chamber, and wherein the chamber is a plasma CVD chamber.

12. (Withdrawn) A chamber cleaning gas according to claim 11 comprising

hexafluoropropylene oxide represented by the formula



13. (Withdrawn) A chamber cleaning gas according to claim 11 comprising  $\text{CF}_3\text{COCF}_3$ .

14. (Withdrawn) A chamber cleaning gas according to claim 11 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar, H<sub>2</sub>, N<sub>2</sub> and O<sub>2</sub>.

15. (Currently Amended) A chamber cleaning method comprising the step of treating a plasma CVD chamber of a semiconductor integrated circuit production device with ~~at least one chamber~~ ~~a~~ cleaning gas selected from the group consisting of  $\text{CF}_3\text{CF}=\text{CF}_2$  and  $\text{CF}_3\text{C}=\text{O}$  to remove reaction byproducts selected from the group consisting of silicon, polysilicon, tungsten, titanium and their oxides, nitrides and carbides attached to the wall of the chamber.

16. (Canceled).

17. (Canceled).

18. (Previously Presented) A chamber cleaning method according to claim 15 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar, H<sub>2</sub>, N<sub>2</sub> and O<sub>2</sub>.

19. (Canceled).

20. (Previously Presented) A chamber cleaning method comprising the step of treating a plasma CVD chamber of a semiconductor integrated circuit production device with at least one chamber cleaning gas comprising CF<sub>3</sub>CF=CF<sub>2</sub> to remove

reaction byproducts selected from the group consisting of silicon, polysilicon, tungsten, titanium and their oxides, nitrides and carbides attached to the wall of the chamber.

21. (Withdrawn) A chamber cleaning gas according to claim 11 wherein the chamber cleaning gas is  $\text{CF}_3\text{CF}=\text{CF}_2$ .

22. (Withdrawn) A chamber cleaning gas comprising  $\text{CF}_3\text{CF}=\text{CF}_2$  wherein the chamber cleaning gas removes reaction byproducts selected from the group consisting of silicon, polysilicon, tungsten, titanium and their oxides, nitrides and carbides attached to the wall of the chamber, and wherein the chamber is a plasma CVD chamber.